

MSAFX11P50A

500 Volts
11 Amps
750 mΩ

P-CHANNEL
ENHANCEMENT MODE
POWER MOSFET

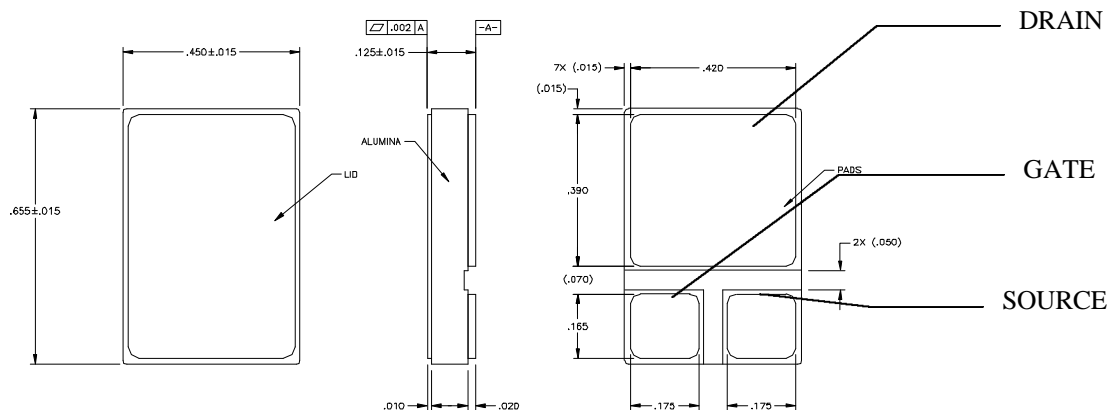
Features

- High voltage p-channel power mosfet; complements MSAFX24N50A
- Ultrafast body diode
- Rugged polysilicon gate cell structure
- Increased Unclamped Inductive Switching (UIS) capability
- Hermetically sealed, surface mount power package
- Low package inductance
- Very low thermal resistance
- Reverse polarity available upon request

Maximum Ratings @ 25°C (unless otherwise specified)

DESCRIPTION	SYMBOL	MAX.	UNIT
Drain-to-Source Breakdown Voltage (Gate Shorted to Source) @ T _J ≥ 25°C	BV _{DSS}	500	Volts
Drain-to-Gate Breakdown Voltage @ T _J ≥ 25°C, R _{GS} = 1 MΩ	BV _{DGR}	500	Volts
Continuous Gate-to-Source Voltage	V _{GS}	+/-20	Volts
Transient Gate-to-Source Voltage	V _{GSM}	+/-30	Volts
Continuous Drain Current 100°C	I _{D25} I _{D100}	11 8	Amps
Peak Drain Current, pulse width limited by T _{Jmax}	I _{DM}	44	Amps
Repetitive Avalanche Current	I _{AR}	11	Amps
Repetitive Avalanche Energy	E _{AR}	30	mJ
Single Pulse Avalanche Energy	E _{AS}	tbd	mJ
Voltage Rate of Change of the Recovery Diode @ I _S ≤ I _{DM} , di/dt ≤ 100 A/μs, V _{DD} ≤ V _{DSS} , T _J ≤ 150°C	dv/dt	5.0	V/ns
Power Dissipation	P _D	300	Watts
Junction Temperature Range	T _J	-55 to +150	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Continuous Source Current (Body Diode)	I _S	11	Amps
Pulse Source Current (Body Diode)	I _{SM}	44	Amps
Thermal Resistance, Junction to Case	θ _{JC}	0.25	°C/W

Mechanical Outline



Electrical Parameters @ 25°C (unless otherwise specified)

DESCRIPTION	SYMBOL	CONDITIONS	MIN	TYP.	MAX	UNIT
Drain-to-Source Breakdown Voltage (Gate Shorted to Source)	BV_{DSS}	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	500			V
Temperature Coefficient of the Drain-to-Source Breakdown Voltage	$\Delta BV_{DSS}/\Delta T_J$			0.054		%/°C
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0		4.5	V
Temperature Coefficient of the Threshold Voltage	$\Delta V_{GS(th)}/\Delta T_J$			0.12		%/°C
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V_{DC}, V_{DS} = 0\text{ V}, T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$			± 100 ± 200	nA
Drain-to-Source Leakage Current (Zero Gate Voltage Drain Current)	I_{DSS}	$V_{DS} = 0.8 \cdot BV_{DSS}, T_J = 25^\circ\text{C}$ $V_{GS} = 0\text{ V}, T_J = 125^\circ\text{C}$			200 1000	μA
Static Drain-to-Source On-State Resistance (1)	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 6\text{ A}, T_J = 25^\circ\text{C}$ $I_D = 6\text{ A}, T_J = 125^\circ\text{C}$		1.4	0.75	Ω
Temperature Coefficient of the Drain-to-Source Resistance	$\Delta R_{DS(on)}/\Delta T_J$			0.6		%/°C
Forward Transconductance (1)	g_{fs}	$V_{DS} \geq 10\text{ V}; I_D = 11\text{ A}$	5	9		S
Input Capacitance Output Capacitance Reverse Transfer Capacitance	C_{iss} C_{oss} C_{rss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		4700 430 135		pF
Turn-on Delay Time Rise Time Turn-off Delay Time Fall Time	$T_{d(on)}$ t_r $t_{d(off)}$ t_f	$V_{GS} = 10\text{ V}, V_{DS} = 250\text{ V},$ $I_D = 6\text{ A}, R_G = 2.00\ \Omega$		33 27 35 35		ns
Total Gate Charge Gate-to-Source Charge Gate-to-Drain (Miller) Charge	$Q_{g(on)}$ Q_{gs} Q_{gd}	$V_{GS} = 10\text{ V}, V_{DS} = 250\text{ V}, I_D = 6\text{ A}$		160 50 95		nC
Body Diode Forward Voltage (1)	V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$			3	V
Reverse Recovery Time (Body Diode)	t_{rr}	$I_F = 10\text{ A}, 25\text{ C}$ $-di/dt = 100\text{ A}/\mu\text{s}, 125\text{ C}$			500 tbd	ns
Reverse Recovery Charge	Q_{rr}	$I_F = 10\text{ A}, 25\text{ C}$ $di/dt = 100\text{ A}/\mu\text{s}, 125\text{ C}$			tbd tbd	μC

Notes

- (1) Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $\delta \leq 2\%$
- (2) Microsemi Corp. does not manufacture the mosfet die; contact company for details.